

< C band internally matched power GaAs FET >

MGFC40V5258

5.2 - 5.8 GHz BAND / 10W

DESCRIPTION

The MGFC40V5258 is an internally impedance-matched GaAs power FET especially designed for use in 5.2 – 5.8 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation

Internally matched to 50(ohm) system

- High output power
P1dB=10W (TYP.) @f=5.2 – 5.8GHz
- High power gain
GLP=10dB (TYP.) @f=5.2 – 5.8GHz
- High power added efficiency
P.A.E.=32% (TYP.) @f=5.2 – 5.8GHz

APPLICATION

- item 01 : 5.2 – 5.8 GHz band power amplifier
- item 51 : 5.2 – 5.8 GHz band digital radio communication

QUALITY

- IG

RECOMMENDED BIAS CONDITIONS

- VDS=10V • ID=2.4A • RG=50ohm

Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain breakdown voltage	-15	V
VGSO	Gate to source breakdown voltage	-15	V
ID	Drain current	7.5	A
IGR	Reverse gate current	-20	mA
IGF	Forward gate current	42	mA
PT *1	Total power dissipation	42.8	W
Tch	Channel temperature	175	°C
Tstg	Storage temperature	-65 to +175	°C

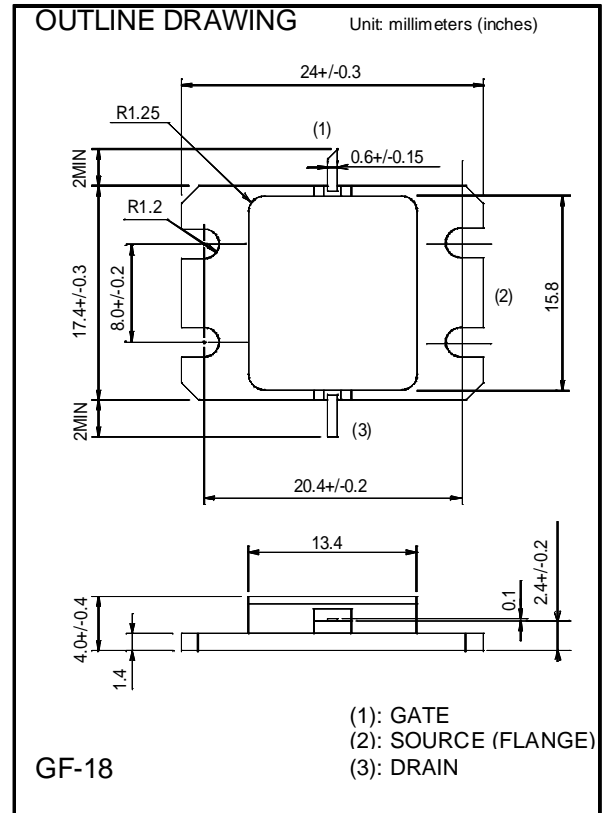
*1 : Tc=25°C

Electrical characteristics (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IDSS	Saturated drain current	VDS=3V, VGS=0V	-	4.5	6	A
gm	Transconductance	VDS=3V, ID=2.2A	-	2	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V, ID=40mA	-2	-3	-4	V
P1dB	Output power at 1dB gain compression	VDS=10V, ID(RF off)=2.4A	39.5	40.5	-	dBm
GLP	Linear Power Gain	f=5.2 – 5.8GHz	8	10	-	dB
ID	Drain current		-	2.4	-	A
P.A.E.	Power added efficiency		-	32	-	%
Rth(ch-c) *3	Thermal resistance		-	-	3.5	°C/W

*2 : item -51 , 2 tone test, Po=29dBm Single Carrier Level, f=5.0GHz, delta f=10MHz

*3 : Channel-case



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